

B70NF03L-VB TO263 Datasheet N-Channel 30-V (D-S) MOSFET

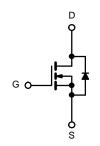
PRODUCT SUMMARY					
V _{DS} (V)	$R_{DS(on)}(\Omega)$	I _D (A) ^{a, e}	Q _g (Typ)		
30	$0.0024 \text{ at V}_{GS} = 10 \text{ V}$	98	82 nC		
	0.0027 at $V_{GS} = 4.5 \text{ V}$	98	02 110		

FEATURES

- Trench Power MOSFET
- 100 % R_g and UIS Tested
- Compliant to RoHS Directive 2011/65/EU







N-Channel MOSFET

APPLICATIONS

- OR-ing
- Server
- DC/DC

Parameter	Symbol	Limit	Unit	
Drain-Source Voltage	V _{DS}	30	V	
Gate-Source Voltage	V _{GS}	± 20	V	
	T _C = 25 °C		98 ^{a, e}	
Continuous Proin Current /T = 175 °C)	T _C = 70 °C		98 ^e	
Continuous Drain Current (T _J = 175 °C)	T _A = 25 °C	I _D	28.8 ^{b, c}	A
	T _A = 70 °C		27 ^{b, c}	^
Pulsed Drain Current	I _{DM}	300		
Avalanche Current Pulse		I _{AS}	36	
Single Pulse Avalanche Energy	L = 0.1 mH	E _{AS}	64.8	V
Continuous Source-Drain Diode Current	T _C = 25 °C	I.	90 ^{a, e}	A
Continuous Source-Diam Diode Current	T _A = 25 °C	l _S —	3.13 ^{b, c}	
	T _C = 25 °C		250 ^a	
Mariana Bana Birahati	T _C = 70 °C	В	175	
Maximum Power Dissipation	T _A = 25 °C	P _D	3.75 ^{b, c}	W
	T _A = 70 °C		2.63 ^{b, c}	
Operating Junction and Storage Temperature Ra	ange	T _J , T _{stg}	- 55 to 175	°C

THERMAL RESISTANCE RATINGS						
Parameter		Symbol	Тур.	Max.	Unit	
Maximum Junction-to-Ambient ^{b, d}	t ≤ 10 sec	R _{thJA}	32	40	°C/W	
Maximum Junction-to-Case	Steady State	R _{thJC}	0.5	0.6]	

Notes:

- a. Based on T_C = 25 °C.
 b. Surface mounted on 1" x 1" FR4 board.

- b. Striate informed on 1 X 1 114 board.
 c. t = 10 sec.
 d. Maximum under steady state conditions is 90 °C/W.
 e. Calculated based on maximum junction temperature. Package limitation current is 90 A.



Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit	
Static							
Drain-Source Breakdown Voltage	V _{DS}	$V_{GS} = 0 \text{ V, } I_D = 250 \mu\text{A}$	30			V	
V _{DS} Temperature Coefficient	$\Delta V_{DS}/T_{J}$	I _D = 250 μA		35		mV/°C	
V _{GS(th)} Temperature Coefficient	$\Delta V_{GS(th)}/T_J$	ι _D = 230 μΑ		- 7.5			
Gate-Source Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	1.5		2.5	V	
Gate-Source Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			± 100	nA	
Zero Gate Voltage Drain Current	1	V _{DS} = 30 V, V _{GS} = 0 V			1	μA	
	IDSS	$V_{DS} = 30 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55 ^{\circ}\text{C}$	10		10		
On-State Drain Current ^a	I _{D(on)}	$V_{DS} \ge 5 \text{ V}, V_{GS} = 10 \text{ V}$	90			Α	
		$V_{GS} = 10 \text{ V}, I_D = 28.8 \text{ A}$		0.0024		_	
Drain-Source On-State Resistance ^a	R _{DS(on)}	$V_{GS} = 4.5 \text{ V}, I_D = 27 \text{ A}$		0.0027		Ω	
Forward Transconductance ^a	g _{fs}	V _{DS} = 15 V, I _D = 28.8 A		160		S	
Dynamic ^b			l				
Input Capacitance	C _{iss}			12065		pF	
Output Capacitance	C _{oss}	$V_{DS} = 15 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$		1725			
Reverse Transfer Capacitance	C _{rss}			970			
Total Gate Charge	Qg	$V_{DS} = 15 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 28.8 \text{ A}$		171	257	nC	
				81.5	123		
Gate-Source Charge	Q_{gs}	$V_{DS} = 15 \text{ V}, V_{GS} = 4.5 \text{ V}, I_D = 28.8 \text{ A}$		34			
Gate-Drain Charge	Q_{gd}			29			
Gate Resistance	R _g	f = 1 MHz		1.4	2.1	Ω	
Turn-On Delay Time	t _{d(on)}			18	27		
Rise Time	t _r	V_{DD} = 15 V, R_L = 0.625 Ω		11	17		
Turn-Off Delay Time	t _{d(off)}	$I_D \cong 24 \text{ A}, V_{GEN} = 10 \text{ V}, R_g = 1 \Omega$		70	105		
Fall Time	t _f			10	15		
Turn-On Delay Time	t _{d(on)}			55	83	ns -	
Rise Time	t _r	V_{DD} = 15 V, R_L = 0.67 Ω		180	270		
Turn-Off Delay Time	t _{d(off)}	$I_D\cong 22.5 \text{ A}, V_{GEN}=4.5 \text{ V}, R_g=1 \Omega$		55	83		
Fall Time	t _f			12	18		
Drain-Source Body Diode Characteristic	s						
Continuous Source-Drain Diode Current	I _S	$T_C = 25 ^{\circ}C$			90	۸	
Pulse Diode Forward Current ^a	I _{SM}				90	A	
Body Diode Voltage	V_{SD}	I _S = 22 A		0.8	1.2	V	
Body Diode Reverse Recovery Time	t _{rr}			52	78	ns	
Body Diode Reverse Recovery Charge	Q _{rr}	I _F = 20 A, di/dt = 100 A/μs, T _{.1} = 25 °C		70.2	105	nC	
Reverse Recovery Fall Time	t _a	$I_F = 20 \text{ A}$, $I_{I} = 100 \text{ A/}\mu\text{s}$, $I_{J} = 25 ^{-1}\text{C}$		27			
Reverse Recovery Rise Time	t _b	7		25		ns	

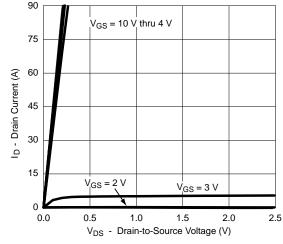
Notes:

- a. Pulse test; pulse width $\leq 300~\mu s,$ duty cycle $\leq 2~\%.$
- b. Guaranteed by design, not subject to production testing.

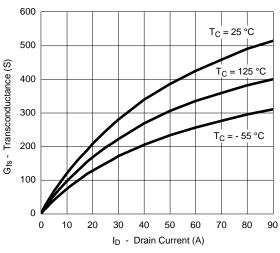
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



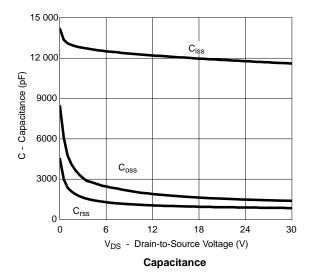
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

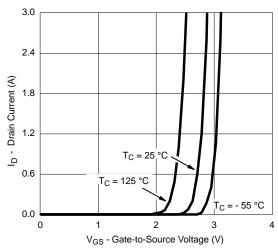


Output Characteristics

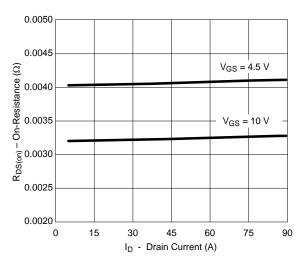


Transconductance

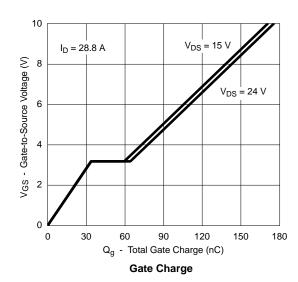




Transfer Characteristics

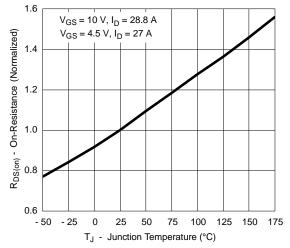


R_{DS(on)} vs. Drain Current

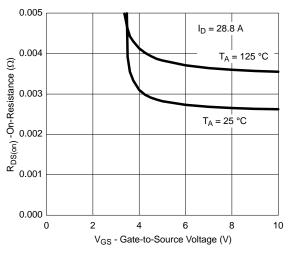




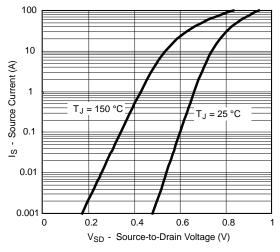
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



On-Resistance vs. Junction Temperature



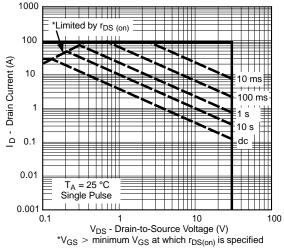
 $R_{DS(on)}$ vs. V_{GS} vs. Temperature



Forward Diode Voltage vs. Temperature



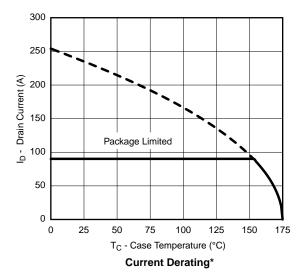
Threshold Voltage



Safe Operating Area, Junction-to-Ambient



TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)





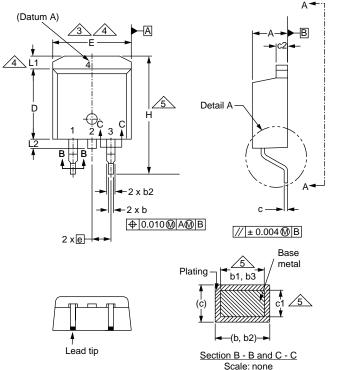
*The power dissipation P_D is based on $T_{J(max)}$ = 175 °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

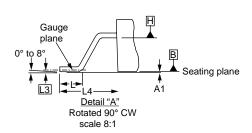


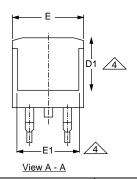
Normalized Thermal Transient Impedance, Junction-to-Case



TO-263AB (HIGH VOLTAGE)







			Scale:
MILLIMETERS		INC	HES
MIN.	MAX.	MIN.	MAX.
4.06	4.83	0.160	0.190
0.00	0.25	0.000	0.010
0.51	0.99	0.020	0.039
0.51	0.89	0.020	0.035
1.14	1.78	0.045	0.070
1.14	1.73	0.045	0.068
0.38	0.74	0.015	0.029

0.015

0.045

0.330

0.023

0.065

0.380

MILLIMETERS		INCHES	
MIN.	MAX.	MIN.	MAX.
6.86	-	0.270	-
9.65	10.67	0.380	0.420
6.22	-	0.245	i
2.54 BSC		0.100 BSC	
14.61	15.88	0.575	0.625
1.78	2.79	0.070	0.110
-	1.65	-	0.066
-	1.78	-	0.070
0.25 BSC		0.010	BSC
4.78	5.28	0.188	0.208
	MIN. 6.86 9.65 6.22 2.54 14.61 1.78 - 0.25	MIN. MAX. 6.86 - 9.65 10.67 6.22 - 2.54 BSC 14.61 15.88 1.78 2.79 - 1.65 - 1.78 0.25 BSC	MIN. MAX. MIN. 6.86 - 0.270 9.65 10.67 0.380 6.22 - 0.245 2.54 BSC 0.100 14.61 15.88 0.575 1.78 2.79 0.070 - 1.65 - - 1.78 - 0.25 BSC 0.010

8.38 ECN: S-82110-Rev. A, 15-Sep-08

0.38

1.14

DWG: 5970

c2

D

DIM. Α Α1 b b1 b2 b3 С с1

Notes

1. Dimensioning and tolerancing per ASME Y14.5M-1994.

0.58

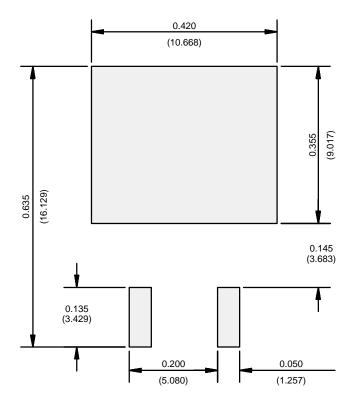
1.65

9.65

- 2. Dimensions are shown in millimeters (inches).
- 3. Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outmost extremes of the plastic body at datum A.
- 4. Thermal PAD contour optional within dimension E, L1, D1 and E1.
- 5. Dimension b1 and c1 apply to base metal only.
- 6. Datum A and B to be determined at datum plane H.
- 7. Outline conforms to JEDEC outline to TO-263AB.



RECOMMENDED MINIMUM PADS FOR D²PAK: 3-Lead



Recommended Minimum Pads Dimensions in Inches/(mm)



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